

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Katoh, T. et al.

Serial No.: 09/711,504

Group Art Unit: 2814

Filed: November 14, 2000

Examiner: Sefer, A.

For: THIN FILM TRANSISTOR AND FABRICATION METHOD OF THE SAME

**EXCESS CLAIM FEE PAYMENT LETTER**

Sir:

Transmitted herewith is an amendment in the above-identified application. The fee has been calculated and is transmitted as shown below.

	<u>AFTER AMENDMENT</u>	<u>PREV. PAID FOR</u>	<u>EXTRA CLAIMS PRESENT</u>	<u>RATE</u>	<u>FEE DUE</u>
Total Claims	18 -	20	= 0	x \$18.00	\$ .00
Indep. Claims	7 -	6	= 1	x \$84.00	\$ 84.00

**TOTAL ADDITIONAL FEE FOR THIS AMENDMENT**


**\$ 84.00**

A check in the amount of \$84.00 to cover the excess claim fees. A duplicate copy of this sheet is enclosed. The Commissioner is authorized charge any deficiencies in fees and credit any overpayment of fees to Attorney's Deposit Account No. 50-0481.

Respectfully Submitted,

Date:

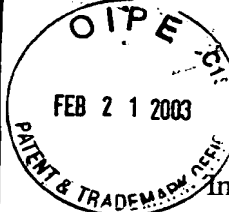
2/21/03



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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

2826  
#128  
Amend.  
S Davis  
3/4/03

In re Application of

Katoh, T. et al.

Serial No.: 09/711,504 ✓

Group Art Unit: 2826

Filed: November 14, 2000 ✓

Examiner: Sefer, A.

For: THIN FILM TRANSISTOR AND FABRICATION METHOD ✓ OF THE SAME

Honorable Commissioner of Patents  
Washington, D.C. 20231

AMENDMENT UNDER 37 C.F.R. §1.111

Sir:

In response to the Office Action dated October 21, 2002, please amend the above-identified application as follows:

IN THE CLAIMS:

Please cancel claims 17-23 without prejudice or disclaimer:

Please amend the claims as follows:

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FEB 26 2003  
TECHNOLOGY CENTER 2800

- 1 4. (Amended) A thin film transistor including:
- 2 a back channel electrode,
- 3 wherein a voltage of a front channel positioned on the side of a gate wiring of said
- 4 thin film transistor is made equal to a voltage of said back channel positioned on the side of a
- 5 back channel electrode by short-circuiting said back channel electrode to a gate electrode
- 6 through a contact-hole provided in a portion of a semiconductor layer forming said thin film
- 7 transistor, and
- 8 wherein said contact-hole is formed in a location remote from an active region of said
- 9 thin film transistor by at least five microns.